

SEMICONDUCTOR STRUCTURE

ABSTRACT

A semiconductor structure is provided, including several first patterns located in a photoresist layer with a thickness greater than 1.2 μm and arranged in a first direction, and several second patterns arranged in a second direction. The first direction and the second direction have an included angle. The first patterns have a first arrangement length in the first direction. The second patterns have a second arrangement length in the second direction. An area sum of the first patterns and the second patterns is less than $1/2$ of a product of the first arrangement length and the second arrangement length.

[Fig. 1]